

PMV160UP

20 V, 1.2 A P-channel Trench MOSFET

Rev. 2 — 6 December 2011

Product data sheet

1. Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 1.8 V R_{DSon} rated
- Trench MOSFET technology
- Very fast switching

1.3 Applications

- Relay driver
- High-side loadswitch
- High-speed line driver
- Switching circuits

1.4 Quick reference data

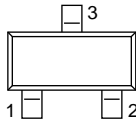
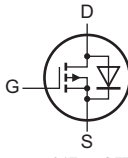
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$	-	-	-20	V
V_{GS}	gate-source voltage		-8	-	8	V
I_D	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	-1.2	A
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = -4.5\text{ V}; I_D = -1.2\text{ A}; T_j = 25\text{ °C}$	-	170	210	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>SOT23 (TO-236AB)</p>	 <p>017aaa257</p>
2	S	source		
3	D	drain		



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3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PMV160UP	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMV160UP	NH%

[1] % = placeholder for manufacturing site code

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$	-	-20	V
V_{GS}	gate-source voltage		-8	8	V
I_D	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-1.2	A
		$V_{GS} = -4.5\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-0.8	A
I_{DM}	peak drain current	$T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$	-	-4	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	335	mW
			[1]	480	mW
		$T_{sp} = 25\text{ °C}$		2170	mW
T_j	junction temperature		-55	150	°C
T_{amb}	ambient temperature		-55	150	°C
T_{stg}	storage temperature		-65	150	°C
Source-drain diode					
I_S	source current	$T_{amb} = 25\text{ °C}$	[1]	-0.5	A

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ }^\circ C$	-0.45	-0.7	-0.95	V
I_{DSS}	drain leakage current	$V_{DS} = -20 V$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	-1	μA
		$V_{DS} = -20 V$; $V_{GS} = 0 V$; $T_j = 150 \text{ }^\circ C$	-	-	-10	μA
I_{GSS}	gate leakage current	$V_{GS} = -8 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	-100	nA
		$V_{GS} = 8 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	-100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 V$; $I_D = -1.2 A$; $T_j = 25 \text{ }^\circ C$	-	170	210	m Ω
		$V_{GS} = -4.5 V$; $I_D = -1.2 A$; $T_j = 150 \text{ }^\circ C$	-	265	328	m Ω
		$V_{GS} = -2.5 V$; $I_D = -1.1 A$; $T_j = 25 \text{ }^\circ C$	-	210	270	m Ω
		$V_{GS} = -1.8 V$; $I_D = -0.5 A$; $T_j = 25 \text{ }^\circ C$	-	280	380	m Ω
g_{fs}	forward transconductance	$V_{DS} = -5 V$; $I_D = -1.2 A$; $T_j = 25 \text{ }^\circ C$	-	3.7	-	S
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = -10 V$; $I_D = -1 A$; $V_{GS} = -4.5 V$; $T_j = 25 \text{ }^\circ C$	-	3.3	4	nC
Q_{GS}	gate-source charge		-	1	-	nC
Q_{GD}	gate-drain charge		-	0.5	-	nC
C_{iss}	input capacitance	$V_{DS} = -10 V$; $f = 1 \text{ MHz}$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	365	-	pF
C_{oss}	output capacitance		-	42	-	pF
C_{rss}	reverse transfer capacitance		-	30	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = -10 V$; $V_{GS} = -4.5 V$; $R_{G(ext)} = 6 \text{ } \Omega$; $T_j = 25 \text{ }^\circ C$; $I_D = -1 A$	-	7	-	ns
t_r	rise time		-	26	-	ns
$t_{d(off)}$	turn-off delay time		-	35	-	ns
t_f	fall time		-	17	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = -0.5 A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-0.7	-1.2	V